CLAIMS

1. A sputtering target for a magnetic recording medium, comprising:

a metal phase and an oxide phase,

wherein the metal phase contains, Pt and at least one or more selected from Mn and V, with the balance being Co and incidental impurities; and

wherein the oxide phase contains O and at least one element selected from a group consisting of B, V, Ru, Ti, Si, Ta, Cr, Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr,

wherein the oxide phase contains at least B .

2. The sputtering target for a magnetic recording medium according to Claim 1, containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt and 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

3. A sputtering target for a magnetic recording medium, comprising:

a metal phase and an oxide phase,

wherein the metal phase contains Pt, Ru, at least one or more selected from Mn and V with the balance being Co and incidental impurities; and

wherein the oxide phase contains O and at least one element selected from a group consisting of B, V, Ru, Ti, Si, Ta, Cr, Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr,

wherein the oxide phase contains at least B.

4. The sputtering target for a magnetic recording medium according to Claim 3, containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt, 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V, and more than 0.5 mol% and 30 mol% or less of Ru; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

5. A sputtering target for a magnetic recording medium, comprising:

a metal phase and an oxide phase,

wherein the metal phase contains Pt and at least one or more selected from Mn and V, with the balance being Co and incidental impurities; and

wherein the oxide phase contains an oxide of at least one element selected from B, V, Ru, Ti, Si, Ta, Cr, Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr.

6. The sputtering target for a magnetic recording medium according to Claim 5, containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt and 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

7. A sputtering target for a magnetic recording medium, comprising:

a metal phase and an oxide phase,

wherein the metal phase contains Pt, Ru, at least one or more selected from Mn and V, with the balance being Co and incidental impurities; and

wherein the oxide phase contains an oxide of at least one element selected from B, V, Ru, Ti, Si, Ta, Cr, Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr .

8. The sputtering target for a magnetic recording medium according to Claim 7, containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt, 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V, and more than 0.5 mol% and 30 mol% or less of Ru; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.